# **Dual 4-Input NAND Gates**

The MC14012B dual 4-input NAND gates are constructed with P-Channel and N-Channel enhancement mode devices in a single monolithic structure (Complementary MOS). Their primary use is where low power dissipation and/or high noise immunity is desired.

## Features

- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- All Outputs Buffered
- Capable of Driving Two Low–Power TTL Loads or One Low–Power Schottky TTL Load Over the Rated Temperature Range
- Double Diode Protection on All Inputs
- Pin-for-Pin Replacements for Corresponding CD4000 Series B Suffix Devices
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable
- This Device is Pb-Free and is RoHS Compliant

### MAXIMUM RATINGS (Voltages Referenced to VSS)

Symbol	Parameter	Value	Unit
V <sub>DD</sub>	DC Supply Voltage Range	-0.5 to +18.0	V
V <sub>in</sub> , V <sub>out</sub>	Input or Output Voltage Range (DC or Transient)	–0.5 to V <sub>DD</sub> + 0.5	V
I <sub>in</sub> , I <sub>out</sub>	Input or Output Current (DC or Transient) per Pin	±10	mA
PD	Power Dissipation, per Package (Note 1)	500	mW
T <sub>A</sub>	Ambient Temperature Range	-55 to +125	°C
T <sub>stg</sub>	Storage Temperature Range	-65 to +150	°C
ΤL	Lead Temperature (8–Second Soldering)	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Temperature Derating: "D/DW" Package: -7.0 mW/°C From 65°C To 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range  $V_{SS} \leq (V_{in} \text{ or } V_{out}) \leq V_{DD}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either  $V_{SS}$  or  $V_{DD}$ ). Unused outputs must be left open.



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SOIC-14 D SUFFIX CASE 751A

### MARKING DIAGRAM



A= Assembly LocationWL, L= Wafer LotYY, Y= YearWW, W= Work WeekG= Pb-Free Package

## ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

## MC14012B **Dual 4–Input NAND Gate**

$IN 4_A D 5$ 10 D IN 2 <sub>B</sub>	$\begin{array}{c}3\\4\\5\\10\\11\\12\\12\\12\\12\\12\\12\\12\\12\\12\\12\\12\\12\\$
NC $\begin{bmatrix} 6 & 9 \end{bmatrix}$ IN 1 <sub>B</sub>	NC = 6, 8
V <sub>SS</sub> $\begin{bmatrix} 7 & 8 \end{bmatrix}$ NC	$V_{DD}$ = PIN 14
NC = NO CONNECTION	$V_{SS}$ = PIN 7
Figure 1. Pin Assignment	Figure 2. Logic Diagram

### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC14012BDG	SOIC-14 (Pb-Free)	55 Units / Rail
NLV14012BDG*	SOIC-14 (Pb-Free)	55 Units / Rail
MC14012BDR2G	SOIC-14 (Pb-Free)	2500 Units / Tape & Reel
NLV14012BDR2G*	SOIC-14 (Pb-Free)	2500 Units / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
 \*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP

Capable.

				-55	5°C		25°C		125	5°C	
Characteristic		Symbol	V <sub>DD</sub> Vdc	Min	Max	Min	Typ (Note 2)	Max	Min	Max	Unit
Output Voltage $V_{in} = V_{DD} \text{ or } 0$	"0" Level	V <sub>OL</sub>	5.0 10 15	- - -	0.05 0.05 0.05	- - -	0 0 0	0.05 0.05 0.05	- - -	0.05 0.05 0.05	Vdc
$V_{in} = 0 \text{ or } V_{DD}$	"1" Level	V <sub>OH</sub>	5.0 10 15	4.95 9.95 14.95	- - -	4.95 9.95 14.95	5.0 10 15	- - -	4.95 9.95 14.95	- - -	Vdc
Input Voltage $(V_O = 4.5 \text{ or } 0.5 \text{ Vdc})$ $(V_O = 9.0 \text{ or } 1.0 \text{ Vdc})$ $(V_O = 13.5 \text{ or } 1.5 \text{ Vdc})$	"0" Level	VIL	5.0 10 15	_ _ _	1.5 3.0 4.0	_ _ _	2.25 4.50 6.75	1.5 3.0 4.0	_ _ _	1.5 3.0 4.0	Vdc
$(V_{O} = 0.5 \text{ or } 4.5 \text{ Vdc})$ $(V_{O} = 1.0 \text{ or } 9.0 \text{ Vdc})$ $(V_{O} = 1.5 \text{ or } 13.5 \text{ Vdc})$	"1" Level	V <sub>IH</sub>	5.0 10 15	3.5 7.0 11	_ _ _	3.5 7.0 11	2.75 5.50 8.25	_ _ _	3.5 7.0 11	_ _ _	Vdc
$\begin{array}{l} \text{Output Drive Current} \\ (\text{V}_{\text{OH}} = 2.5 \ \text{Vdc}) \\ (\text{V}_{\text{OH}} = 4.6 \ \text{Vdc}) \\ (\text{V}_{\text{OH}} = 9.5 \ \text{Vdc}) \\ (\text{V}_{\text{OH}} = 13.5 \ \text{Vdc}) \end{array}$	Source	I <sub>OH</sub>	5.0 5.0 10 15	-3.0 -0.64 -1.6 -4.2	- - -	-2.4 -0.51 -1.3 -3.4	-4.2 -0.88 -2.25 -8.8	- - -	-1.7 -0.36 -0.9 -2.4	- - -	mAdo
(V <sub>OL</sub> = 0.4 Vdc) (V <sub>OL</sub> = 0.5 Vdc) (V <sub>OL</sub> = 1.5 Vdc)	Sink	I <sub>OL</sub>	5.0 10 15	0.64 1.6 4.2	- - -	0.51 1.3 3.4	0.88 2.25 8.8	- - -	0.36 0.9 2.4	- - -	mAdo
Input Current		l <sub>in</sub>	15	_	±0.1	-	±0.00001	±0.1	_	±1.0	μAdc
Input Capacitance (V <sub>in</sub> = 0)		C <sub>in</sub>	_	-	-	-	5.0	7.5	-	_	pF
Quiescent Current (Per Package)		I <sub>DD</sub>	5.0 10 15	- - -	0.25 0.5 1.0	- - -	0.0005 0.0010 0.0015	0.25 0.5 1.0	- - -	7.5 15 30	μAdc
Total Supply Current (Note (Dynamic plus Quiesce Per Gate, C <sub>L</sub> = 50 pF)		Ι <sub>Τ</sub>	5.0 10 15			$I_{T} = (0.$	3 μΑ/kHz) f 6 μΑ/kHz) f 9 μΑ/kHz) f	+ I <sub>DD</sub> /N	·	-	μAdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
2. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.
3. The formulas given are for the typical characteristics only at 25°C.
4. To calculate total supply current at loads other than 50 pF:

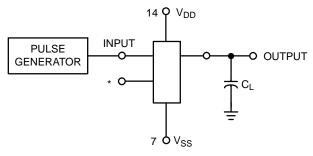
 $I_T(C_L) = I_T(50 \text{ pF}) + (C_L - 50) \text{ Vfk}$ 

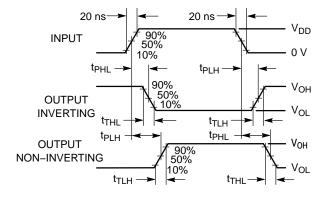
where:  $I_T$  is in  $\mu A$  (per package),  $C_L$  in pF, V = ( $V_{DD} - V_{SS}$ ) in volts, f in kHz is input frequency, and k = 0.001 x the number of exercised gates per package.

## SWITCHING CHARACTERISTICS (Note 5) (CL = 50 pF, TA = $25^{\circ}$ C)

Characteristic	Symbol	V <sub>DD</sub> Vdc	Min	Typ (Note 6)	Max	Unit
Output Rise Time $t_{TLH} = (1.35 \text{ ns/pF}) \text{ C}_L + 33 \text{ ns}$ $t_{TLH} = (0.60 \text{ ns/pF}) \text{ C}_L + 20 \text{ ns}$ $t_{TLH} = (0.40 \text{ ns/PF}) \text{ C}_L + 20 \text{ ns}$	t <sub>TLH</sub>	5.0 10 15	- - -	100 50 40	200 100 80	ns
Output Fall Time t <sub>THL</sub> = (1.35 ns/pF) C <sub>L</sub> + 33 ns t <sub>THL</sub> = (0.60 ns/pF) C <sub>L</sub> + 20 ns t <sub>THL</sub> = (0.40 ns/pF) C <sub>L</sub> + 20 ns	t <sub>THL</sub>	5.0 10 15	_ _ _	100 50 40	200 100 80	ns
Propagation Delay Time $t_{PLH}, t_{PHL} = (0.90 \text{ ns/pF}) \text{ C}_{L} + 115 \text{ ns}$ $t_{PLH}, t_{PHL} = (0.36 \text{ ns/pF}) \text{ C}_{L} + 47 \text{ ns}$ $t_{PLH}, t_{PHL} = (0.26 \text{ ns/pF}) \text{ C}_{L} + 37 \text{ ns}$	t <sub>PLH</sub> , t <sub>PHL</sub>	5.0 10 15	- - -	160 65 50	300 130 100	ns

The formulas given are for the typical characteristics only at 25°C.
 Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.





\*All unused inputs of AND, NAND gates must be connected to  $V_{\text{DD}}.$  All unused inputs of OR, NOR gates must be connected to  $V_{\text{SS}}.$ 

## Figure 3. Switching Time Test Circuit and Waveforms

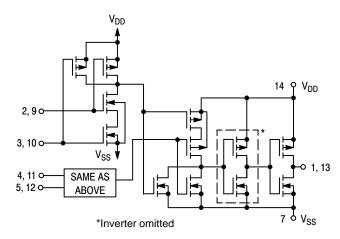


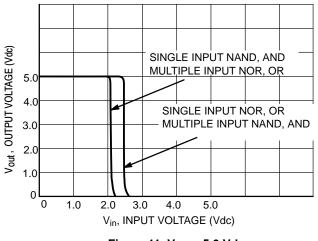
Figure 4. Circuit Schematic – One of Two Gates Shown

### **N-CHANNEL DRAIN CURRENT (SINK) P-CHANNEL DRAIN CURRENT (SOURCE)** -10 5.0 -9.0 -8.0 4.0 $T_A = -55^{\circ}C$ ID, DRAIN CURRENT (mA) ID, DRAIN CURRENT (mA) -7.0 $T_A = -55^{\circ}C$ -40°C 3.0 -6.0 40°C -5.0 +25°C +25°C +85°C +85°C 2.0 -4.0 +125°C -3.0 +125°C -2.0 1.0 -1.0 0 0 1.0 2.0 3.0 4.0 5.0 -2.0 -3.0 -4.0 -5.0 0 -1.0 0 V<sub>DS</sub>, DRAIN-TO-SOURCE VOLTAGE (Vdc) V<sub>DS</sub>, DRAIN-TO-SOURCE VOLTAGE (Vdc) Figure 6. V<sub>GS</sub> = - 5.0 Vdc Figure 5. V<sub>GS</sub> = 5.0 Vdc 20 -50 -45 18 $T_A = -55^{\circ}C$ -40 16 ID, DRAIN CURRENT (mA) ID, DRAIN CURRENT (mA) 14 -40°C -35 -55°Ċ +25°C 12 $T_A = \cdot$ -30 +<u>85°C</u> 10 -25 -40°C + 25°C +125°C 8.0 -20 +85°C 6.0 -15 +125°C 4.0 -10 2.0 -5.0 0 0 2.0 3.0 4.0 5.0 6.0 7.0 8.0 -1.0 -2.0 -3.0 -4.0 -5.0 -6.0 -7.0 -8.0 -9.0 -10 1.0 9.0 10 0 0 V<sub>DS</sub>, DRAIN-TO-SOURCE VOLTAGE (Vdc) V<sub>DS</sub>, DRAIN-TO-SOURCE VOLTAGE (Vdc) Figure 7. V<sub>GS</sub> = 10 Vdc Figure 8. V<sub>GS</sub> = - 10 Vdc 50 - 100 45 - 90 40 - 80 ID, DRAIN CURRENT (mA) ID, DRAIN CURRENT (mA) 35 $T_A = -55^{\circ}C$ - 70 30 - 60 -40°C $T_A = -55^{\circ}C$ 25 - 50 +25°C 40°C +85°C +25°C 20 - 40 +85°C +125°C 15 - 30 +125°C 10 - 20 5.0 - 10 0 0 0 4.0 8.0 10 12 14 16 18 -2.0 -4.0 -6.0 -8.0 -10 -12 -14 -16 -18 -20 2.0 6.0 20 0 V<sub>DS</sub>, DRAIN-TO-SOURCE VOLTAGE (Vdc) V<sub>DS</sub>, DRAIN-TO-SOURCE VOLTAGE (Vdc) Figure 9. V<sub>GS</sub> = 15 Vdc Figure 10. $V_{GS} = -15$ Vdc

### **TYPICAL B-SERIES GATE CHARACTERISTICS**

These typical curves are not guarantees, but are design aids. Caution: The maximum rating for output current is 10 mA per pin.

## **VOLTAGE TRANSFER CHARACTERISTICS**





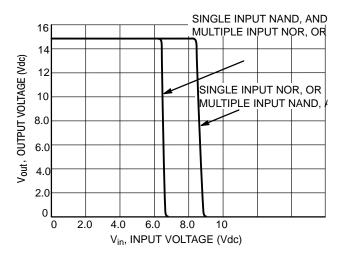
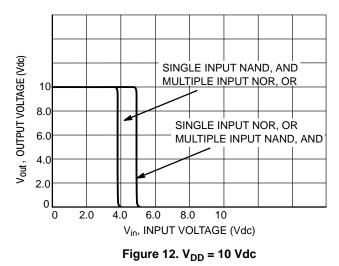


Figure 13. V<sub>DD</sub> = 15 Vdc



### DC NOISE MARGIN

The DC noise margin is defined as the input voltage range from an ideal "1" or "0" input level which does not produce output state change(s). The typical and guaranteed limit values of the input values  $V_{IL}$  and  $V_{IH}$  for the output(s) to be at a fixed voltage  $V_O$  are given in the Electrical Characteristics table.  $V_{IL}$  and  $V_{IH}$  are presented graphically in Figure 11.

Guaranteed minimum noise margins for both the "1" and "0" levels =

1.0 V with a 5.0 V supply 2.0 V with a 10.0 V supply 2.5 V with a 15.0 V supply

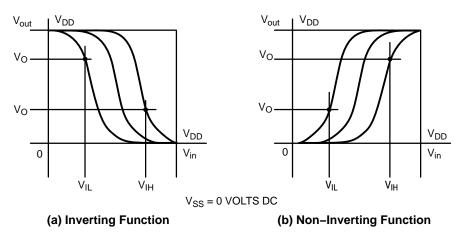


Figure 14. DC Noise Immunity





\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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### SOIC-14 CASE 751A-03 ISSUE L

## DATE 03 FEB 2016

STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 2: CANCELLED	STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE	STYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE
STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE	STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON ANODE 13. ANODE/CATHODE 14. ANODE/CATHODE	STYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE

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